

Features

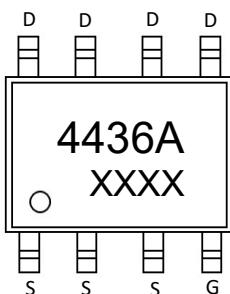
- Low $R_{DS(on)}$ & FOM
- Extremely low switching loss
- Excellent stability and uniformity
- Fast switching and soft recovery

Product Summary

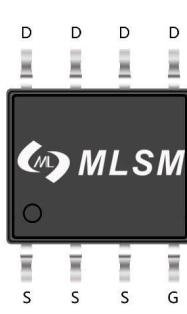
V_{DS}	$R_{DS(ON)}\text{ MAX}$	$I_D\text{ MAX}$
60V	36mΩ@10V	8A
	43mΩ@4.5V	

Application

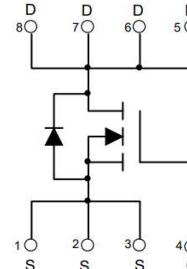
- Power switching application



4436A: Device code
XXXX:Code



SOP-8 top view



Schematic diagram



Pb-Free



RoHS



Halogen-Free

Marking and pin assignment

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit	
Common Ratings (TC=25°C Unless Otherwise Noted)				
V_{DS}	Drain-Source Breakdown Voltage	60	V	
V_{GS}	Gate-Source Voltage	± 20	V	
T_J	Maximum Junction Temperature	150	°C	
T_{STG}	Storage Temperature Range	-50 to 155	°C	
I_S	Diode Continuous Forward Current	8	A	
Mounted on Large Heat Sink				
I_{DM}	Pulse Drain Current Tested	Tc=25°C	36	A
I_D	Continuous Drain Current	Tc=25°C	8	A
P_D	Maximum Power Dissipation	Tc=25°C	2.6	W
$R_{θJA}$	Thermal Resistance Junction-Ambient		40 °C/W	

Ordering Information (Example)

Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
MLSQ4436A	SOP-8	4436A	3,000	6,000	42,000	13" reel

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ T_J = 25°C (unless otherwise stated)						
BV _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	60	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =60V, V _{GS} =0V	-	-	1	uA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.0	1.7	2.5	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =10V, I _D =7.8A	-	22	36	mΩ
		V _{GS} =4.5V, I _D =7.0A	-	30	43	mΩ
Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise stated)						
C _{ISS}	Input Capacitance	V _{DS} =30V, V _{GS} =0V, f=1MHz	-	1050	-	pF
C _{OSS}	Output Capacitance		-	65	-	pF
C _{RSS}	Reverse Transfer Capacitance		-	55	-	pF
Switching Characteristics						
Q _g	Total Gate Charge	V _{DD} =30V, I _D =8A, V _{GS} =10V	-	26	-	nC
Q _{gs}	Gate Source Charge		-	5.7	-	nC
Q _{gd}	Gate Drain Charge		-	5.2	-	nC
t _{d(on)}	Turn-on Delay Time	V _{DD} =30V, I _D =8A, V _{GS} =10V, R _G =3Ω	-	8.4	-	nS
t _r	Turn-on Rise Time		-	8.5	-	nS
t _{d(off)}	Turn-Off Delay Time		-	36	-	nS
t _f	Turn-Off Fall Time		-	5	-	nS
Source-Drain Diode Characteristics						
V _{SD}	Forward on voltage	T _j =25°C, I _S =8A	-	0.8	1.2	V

Typical Operating Characteristics

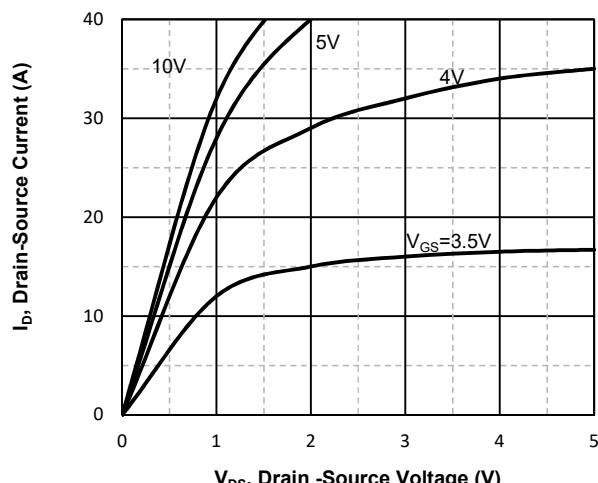


Fig1. Typical Output Characteristics

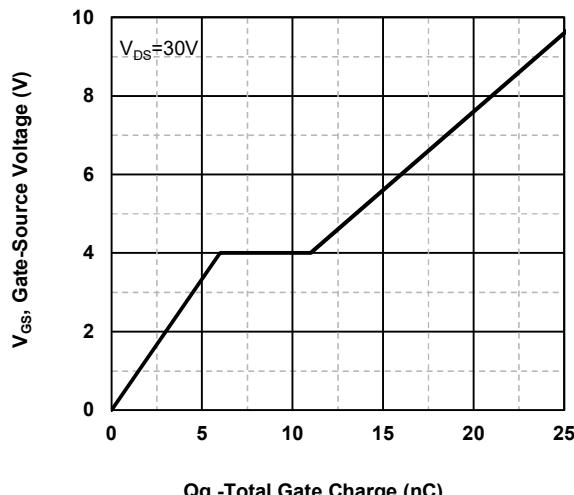


Fig2. Typical Gate Charge Vs.Gate-Source Voltage

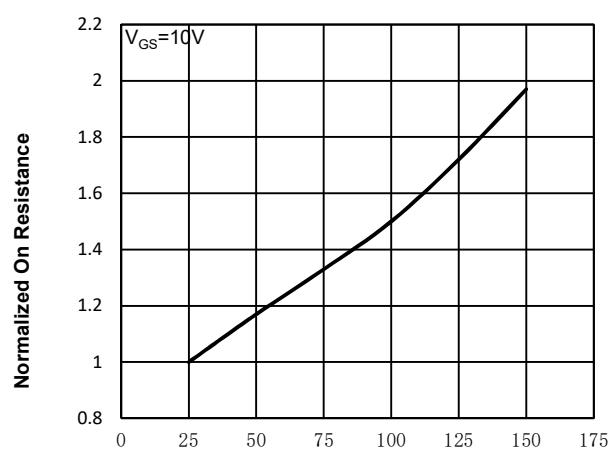


Fig3. Normalized On-Resistance Vs. Temperature

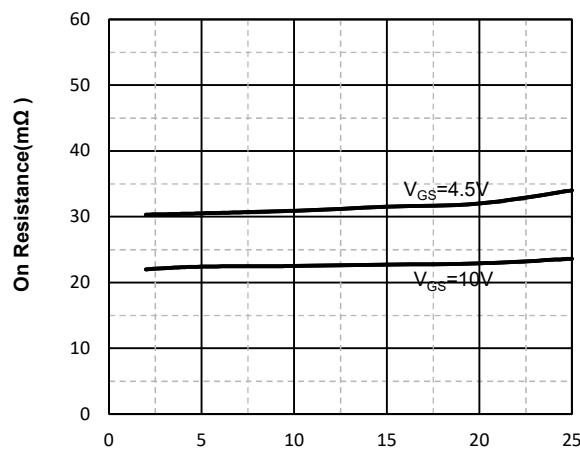


Fig4. On-Resistance Vs. Drain-Source Current

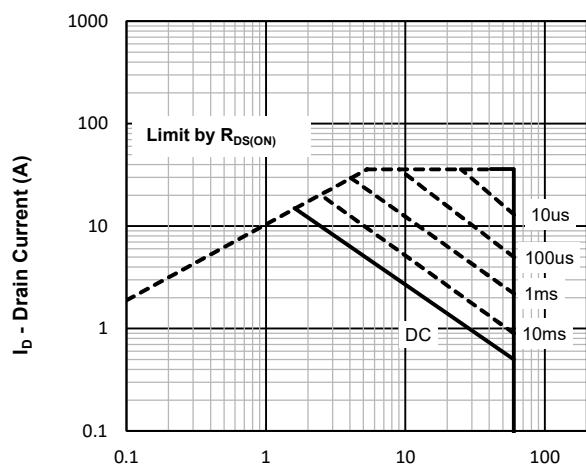


Fig5. Maximum Safe Operating Area

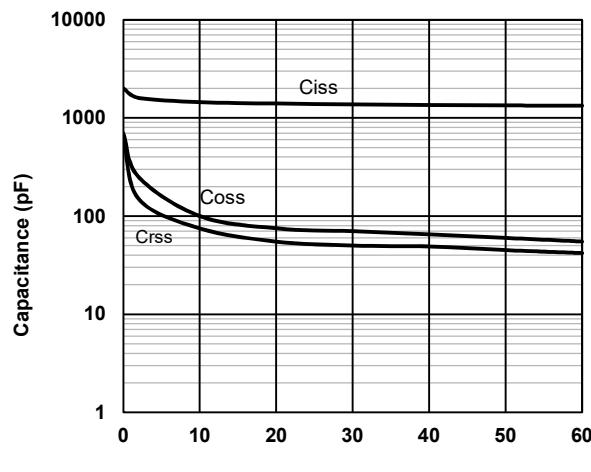
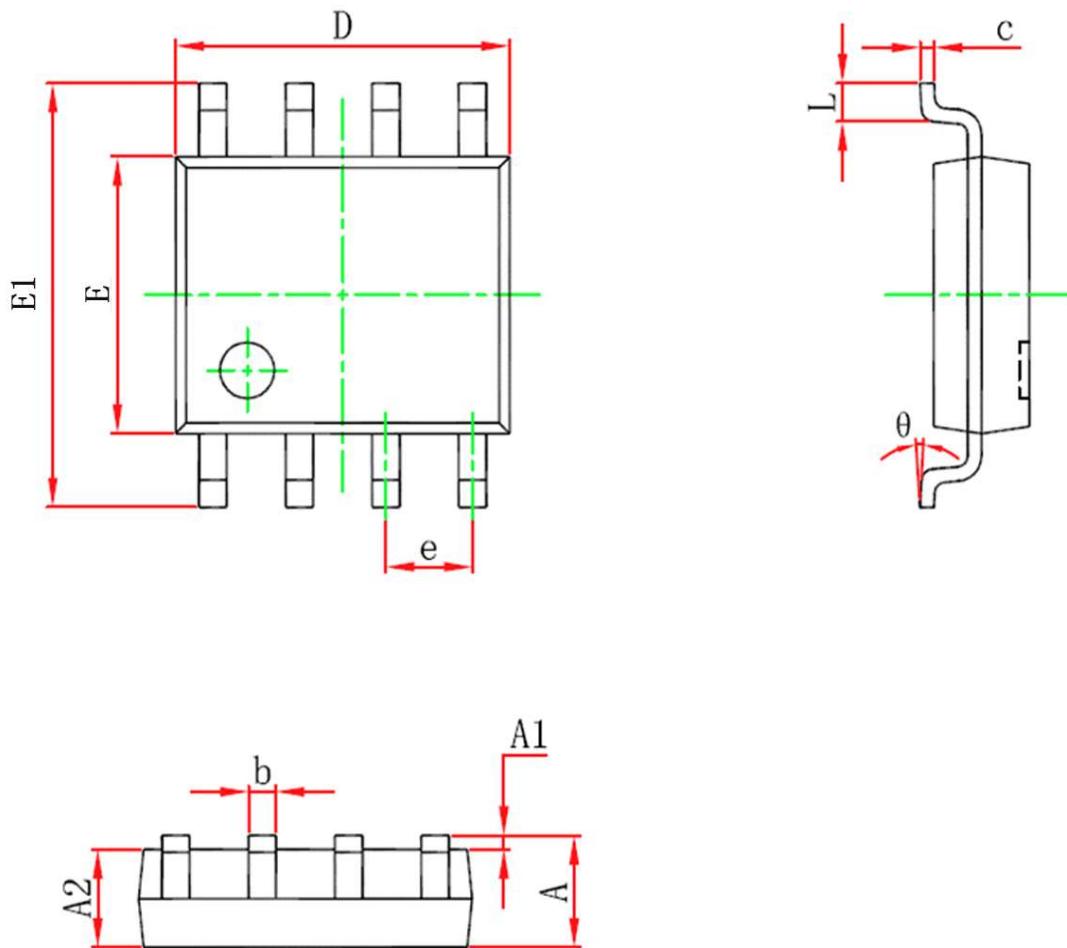


Fig6 Typical Capacitance Vs.Drain-Source

SOP-8 Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	1.450	1.750	0.057	0.068
A1	0.100	0.250	0.003	0.009
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.012	0.020
c	0.170	0.250	0.006	0.009
D	4.700	5.100	0.185	0.200
e	1.270(BSC)		0.050(BSC)	
E	3.800	4.000	0.149	0.157
E1	5.800	6.200	0.228	0.244
L	0.400	1.270	0.015	0.050
θ	0°	8°	0°	8°